

# Thursday, October 4, 2018

<b>MBE Workshop</b> <b>Location: Max Bell 252</b> <b>Workshop Welcome</b> <b>Moderators:</b> Stephanie Law, Amy Liu, Sanjay Krishna	
8:45am	<b>Workshop Welcome</b>
<b>MBE Workshop</b> <b>Location: Max Bell 252</b> <b>2D Materials</b> <b>Moderator:</b> Paul Simmonds	
9:00am	Christopher Hinkle, University of Texas Dallas, 2D materials growth for vertically integrated nanoelectronics
9:30am	Roland Kawakami, The Ohio State University, Room temperature ferromagnetism in epitaxial van der Waals magnets
10:00am	Sergei Novikov, University of Nottingham, High-temperature MBE of Graphene and hBN monolayers
10:30am	<b>Break</b>
<b>MBE Workshop</b> <b>Location: Max Bell 252</b> <b>Layered Heteroepitaxy</b> <b>Moderator:</b> Stephanie Law	
10:45am	Siddharth Rajan, The Ohio State University, Synthesis and Properties of van der Waals-bonded Semiconductor Heterojunctions
11:15am	Jacek Furdyna, University of Notre Dame, Formation of self-assembled layer phases in van der Waals epitaxy
11:45am	Susanne Stemmer, University of California Santa Barbara, Topological Heterostructures by MBE
12:15pm	<b>Lunch</b>
<b>MBE Workshop</b> <b>Location: Max Bell 252</b> <b>Topological Insulators</b> <b>Moderator:</b> James Gupta	
1:30pm	Maria Tamargo, City College of New York, MBE Growth of topological insulator hetero-nanostructures
2:00pm	Stephanie Law, University of Delaware, Buffer layers for improved topological insulator growth
2:30pm	Anthony Richardella, Penn State, Disorder and Defects in Magnetic Topological Insulator Films with Quantized Edge State Transport
3:00pm	<b>Break</b>
<b>MBE Workshop</b> <b>Location: Max Bell 252</b> <b>Low Bandgap Antimonides</b> <b>Moderator:</b> Mike Santos	
3:15pm	Roberto Myers, The Ohio State University, Spin-orbit driven thermo-electric transport in InSb: approaches for band engineered topological heterostructures
3:45pm	Minh Nguyen, HRL Laboratories, Non-topological edge states in InAs/GaSb topological quantum well
4:15pm	Sergey Suchalkin, SUNY Stony Brook, HRL Laboratories, Metamorphic strain-compensated InSb/InAsSb superlattices with ultra thin layers

# Friday, October 5, 2018

<b>MBE Workshop</b> <b>Location: Max Bell 252</b> <b>Crosscutting</b> <b>Moderator: Sanjay Krishna</b>	
9:00am	Zbig Wasilewski, University of Waterloo, In pursuit of perfect morphology: metamorphic buffers and polar directions challenges
9:30am	Steve Ringel, The Ohio State University, Heteroepitaxial Pathways for III-V/Si Photovoltaics
10:00am	Gene Fitzgerald, Massachusetts Institute of Technology, III-V devices in Silicon CMOS circuits: Materials and Processing
10:30am	<b>Break</b>
<b>MBE Workshop</b> <b>Location: Max Bell 252</b> <b>Metamorphic Antimonides</b> <b>Moderator: Amy Liu</b>	
10:45am	Neil Baril, U.S. Army Night Vision & Electronic Sensors Directorate, Growth of InAsSb on metamorphic buffer layers for infrared detectors
11:15am	Stephanie Tomasulo, Naval Research Laboratory, Metamorphic InAsSb on GaSb substrates for long-wavelength infrared applications
11:45am	Tyler Grassman, The Ohio State University, Metamorphic Pathways toward Long-Wavelength InAsSb via MBE and MOCVD
12:15pm	<b>Lunch</b>